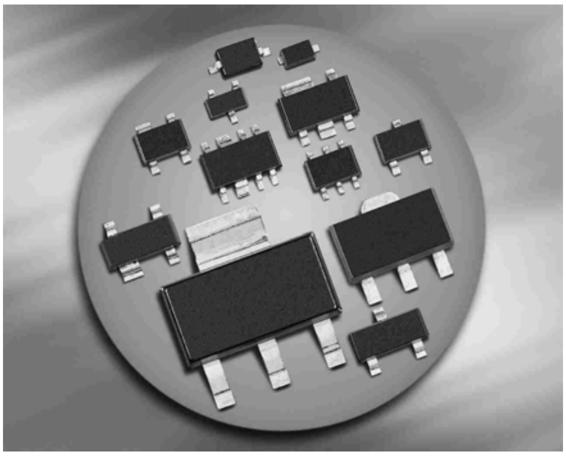
NPN Silicon AF Transistors

- For AF input stages and driver applications
- High current gain
- Low collector-emitter saturation voltage
- Low noise between 30 Hz and 15 kHz
- Complementary types:
  BC856...-BC860...(PNP)



Type	Marking	Pin Configuration						Package
BC846A	1As	1=B	2=E	3=C	-	-	-	SOT23
BC846B	1Bs	1=B	2=E	3=C	-	-	-	SOT23
BC846BW	1Bs	1=B	2=E	3=C	-	-	-	SOT323
BC847A	1Es	1=B	2=E	3=C	-	-	-	SOT23
BC847B	1Fs	1=B	2=E	3=C	-	-	-	SOT23
BC847BF	1Fs	1=B	2=E	3=C	-	-	-	TSFP-3
BC847BL3	1F	1=B	2=E	3=C	-	-	-	TSLP-3-1
BC847BT	1F	1=B	2=E	3=C	-	-	-	SC75
BC847BW	1Fs	1=B	2=E	3=C	-	-	-	SOT323
BC847C	1Gs	1=B	2=E	3=C	-	-	-	SOT23
BC847CW	1Gs	1=B	2=E	3=C	-	-	-	SOT323
BC848A	1Js	1=B	2=E	3=C	-	-	-	SOT23
BC848AW	1Js	1=B	2=E	3=C	-	-	-	SOT323
BC848B	1Ks	1=B	2=E	3=C	-	-	-	SOT23
BC848BF	1Ks	1=B	2=E	3=C	-	-	-	TSFP-3
BC848BL3	1K	1=B	2=E	3=C	-	-	-	TSLP-3-1
BC848BW	1Ks	1=B	2=E	3=C	-	-	-	SOT323
BC848C	1Ls	1=B	2=E	3=C	-	-	-	SOT23
BC848CW	1Ls	1=B	2=E	3=C	-	-	-	SOT323
BC849B	2Bs	1=B	2=E	3=C	-	-	-	SOT23
BC849BF	2Bs	1=B	2=E	3=C	-	-	-	TSFP-3
BC849C	2Cs	1=B	2=E	3=C	-	-	-	SOT23
BC849CW	2Cs	1=B	2=E	3=C	-	-	-	SOT323
BC850B	2Fs	1=B	2=E	3=C	-	-	-	SOT23
BF850BF	2Fs	1=B	2=E	3=C	-	-	-	TSFP-3
BC850BW	2Fs	1=B	2=E	3=C	-	-	-	SOT323
BC850C	2Gs	1=B	2=E	3=C	-	-	-	SOT23
BC850CW	2Gs	1=B	2=E	3=C	-	-	-	SOT323

Maximum Ratings

Parameter	Symbol	Value	Unit
Collector-emitter voltage	V_{CEO}		V
BC846...		65	
BC847..., BC850...		45	
BC848..., BC849...		30	
Collector-emitter voltage	V_{CES}		
BC846...		80	
BC847..., BC850...		50	
BC848..., BC849...		30	
Collector-base voltage	V_{CBO}		
BC846...		80	
BC847..., BC850...		50	
BC848..., BC849...		30	
Emitter-base voltage	V_{EBO}		
BC846...		6	
BC847..., BC850...		6	
BC848..., BC849...		6	
Collector current	I_C	100	mA
Peak collector current	I_{CM}	200	
Total power dissipation-	P_{tot}		mW
$T_S \leq 71$ °C, BC846-BC850		330	
$T_S \leq 128$ °C, BC847F-BC850F		250	
$T_S \leq 135$ °C, BC847L3-BC848L3		250	
$T_S \leq 109$ °C, BC847T		250	
$T_S \leq 124$ °C, BC846W-BC850W		250	
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	-65 ... 150	

Thermal Resistance

Parameter	Symbol	Value	Unit
Junction - soldering point[1]	R_{thJS}		K/W
BC846-BC850		≤ 240	
BC847F-BC850F		≤ 90	
BC847L3-BC848L3		≤ 60	
BC847T		≤ 165	
BC846W-BC850W		≤ 105	

[1]For calculation of R_{thJA} please refer to Application Note Thermal Resistance

Electrical Characteristics at T_A = 25°C, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
DC Characteristics					
Collector-emitter breakdown voltage	$V_{(BR)CEO}$				V
I_C = 10 mA, I_B = 0 , BC846...		65	-	-	
I_C = 10 mA, I_B = 0 , BC847..., BC850...		45	-	-	
I_C = 10 mA, I_B = 0 , BC848..., BC849...		30	-	-	
Collector-base breakdown voltage	$V_{(BR)CBO}$				
I_C = 10 µA, I_E = 0 , BC846...		80	-	-	
I_C = 10 µA, I_E = 0 , BC847..., BC850...		50	-	-	
I_C = 10 µA, I_E = 0 , BC848..., BC849...		30	-	-	
Emitter-base breakdown voltage I_E = 0 , I_C = 10 µA	$V_{(BR)EBO}$	-	6	-	
Collector-base cutoff current	I_{CBO}				µA
V_{CB} = 45 V, I_E = 0		-	0.015	-	
V_{CB} = 30 V, I_E = 0 , T_A = 150 °C		-	5	-	
DC current gain[1]	h_{FE}				-
I_C = 10 µA, V_{CE} = 5 V, h_{FE}-grp.A		-	140	-	
I_C = 10 µA, V_{CE} = 5 V, h_{FE}-grp.B		-	250	-	
I_C = 10 µA, V_{CE} = 5 V, h_{FE}-grp.C		-	480	-	
I_C = 2 mA, V_{CE} = 5 V, h_{FE}-grp.A		110	180	220	
I_C = 2 mA, V_{CE} = 5 V, h_{FE}-grp.B		200	290	450	
I_C = 2 mA, V_{CE} = 5 V, h_{FE}-grp.C		420	520	800	
Collector-emitter saturation voltage[1]	V_{CEsat}				mV
I_C = 10 mA, I_B = 0.5 mA		-	90	250	
I_C = 100 mA, I_B = 5 mA		-	200	600	
Base emitter saturation voltage[1]	V_{BEsat}				
I_C = 10 mA, I_B = 0.5 mA		-	700	-	
I_C = 100 mA, I_B = 5 mA		-	900	-	
Base-emitter voltage[1]	$V_{BE(ON)}$				
I_C = 2 mA, V_{CE} = 5 V		580	660	700	
I_C = 10 mA, V_{CE} = 5 V		-	-	770	

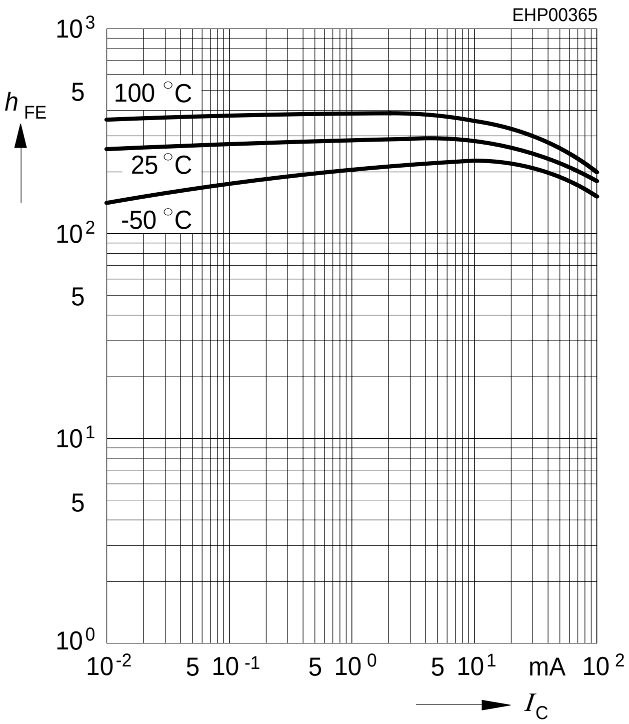
[1]Pulse test: t < 300µs; D < 2%

Electrical Characteristics at T_A = 25°C, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
AC Characteristics					
Transition frequency I_C = 10 mA, V_{CE} = 5 V, f = 100 MHz	f_T	-	250	-	MHz
Collector-base capacitance V_{CB} = 10 V, f = 1 MHz	C_{cb}	-	0.95	-	pF
Emitter-base capacitance V_{EB} = 0.5 V, f = 1 MHz	C_{eb}	-	9	-	
Short-circuit input impedance	h_{11e}				kΩ
I_C = 2 mA, V_{CE} = 5 V, f = 1 kHz, h_{FE}-grp.A		-	2.7	-	
I_C = 2 mA, V_{CE} = 5 V, f = 1 kHz, h_{FE}-grp.B		-	4.5	-	
I_C = 2 mA, V_{CE} = 5 V, f = 1 kHz, h_{FE}-grp.C		-	8.7	-	
Open-circuit reverse voltage transf. ratio	h_{12e}				10^{-4}
I_C = 2 mA, V_{CE} = 5 V, f = 1 kHz, h_{FE}-grp.A		-	1.5	-	
I_C = 2 mA, V_{CE} = 5 V, f = 1 kHz, h_{FE}-grp.B		-	2	-	
I_C = 2 mA, V_{CE} = 5 V, f = 1 kHz, h_{FE}-grp.C		-	3	-	
Short-circuit forward current transf. ratio	h_{21e}				
I_C = 2 mA, V_{CE} = 5 V, f = 1 kHz, h_{FE}-grp.A		-	200	-	
I_C = 2 mA, V_{CE} = 5 V, f = 1 kHz, h_{FE}-grp.B		-	330	-	
I_C = 2 mA, V_{CE} = 5 V, f = 1 kHz, h_{FE}-grp.C		-	600	-	
Open-circuit output admittance	h_{22e}				µS
I_C = 2 mA, V_{CE} = 5 V, f = 1 kHz, h_{FE}-grp.A		-	18	-	
I_C = 2 mA, V_{CE} = 5 V, f = 1 kHz, h_{FE}-grp.B		-	30	-	
I_C = 2 mA, V_{CE} = 5 V, f = 1 kHz, h_{FE}-grp.C		-	60	-	
Noise figure I_C = 200 µA, V_{CE} = 5 V, f = 1 kHz, Δf = 200 Hz, R_S = 2 kΩ, BC849..., BC850...	F	-	1.2	4	dB
Equivalent noise voltage I_C = 200 µA, V_{CE} = 5 V, R_S = 2 kΩ, f = 10 ... 50 Hz , BC850...	V_n	-	-	0.135	µV

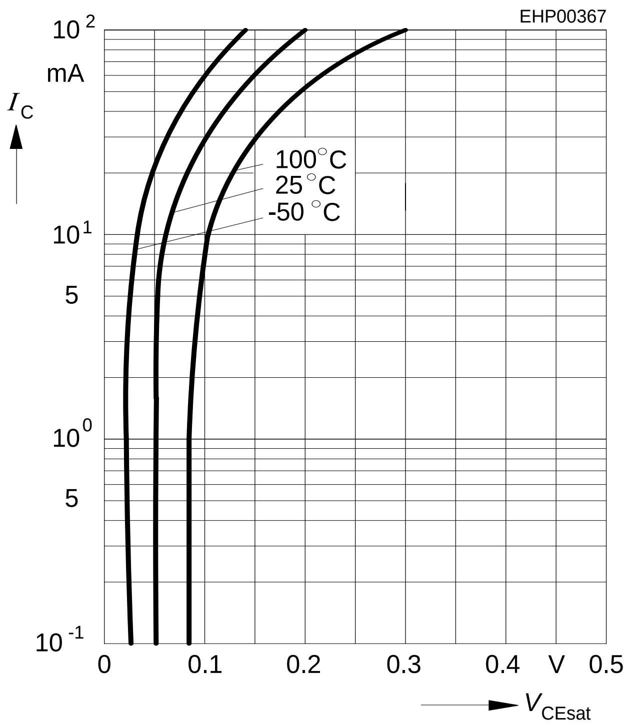
DC current gain $h_{FE} = f(I_C)$

V_{CE} = 5 V



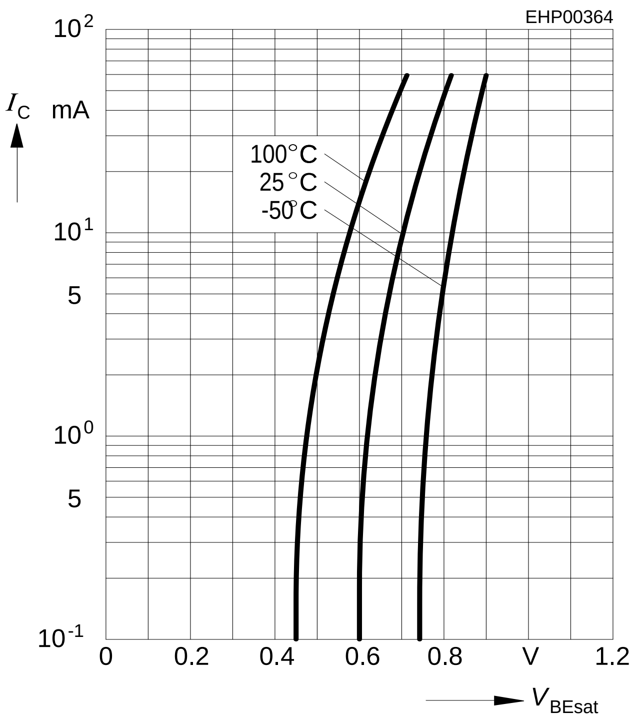
Collector-emitter saturation voltage

$I_C = f(V_{CEsat})$, h_{FE} = 20



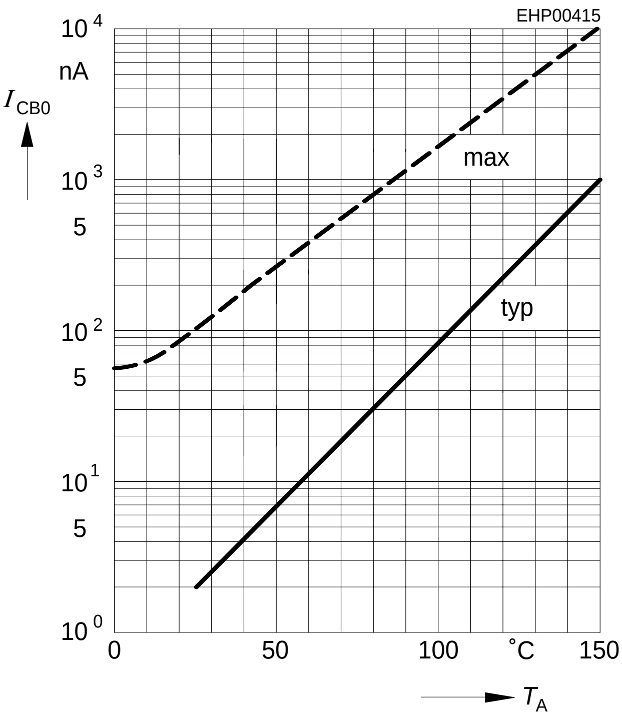
Base-emitter saturation voltage

$I_C = f(V_{BEsat})$, h_{FE} = 20



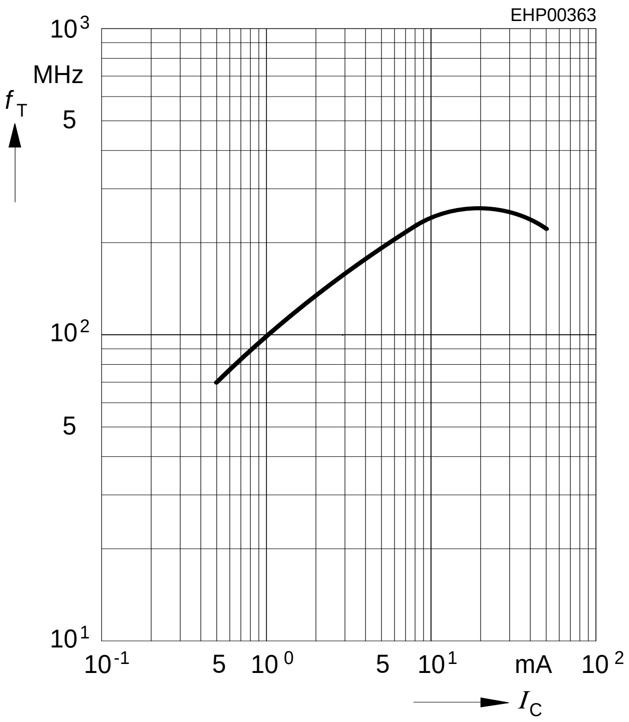
Collector cutoff current $I_{CBO} = f(T_A)$

V_{CB} = 30 V



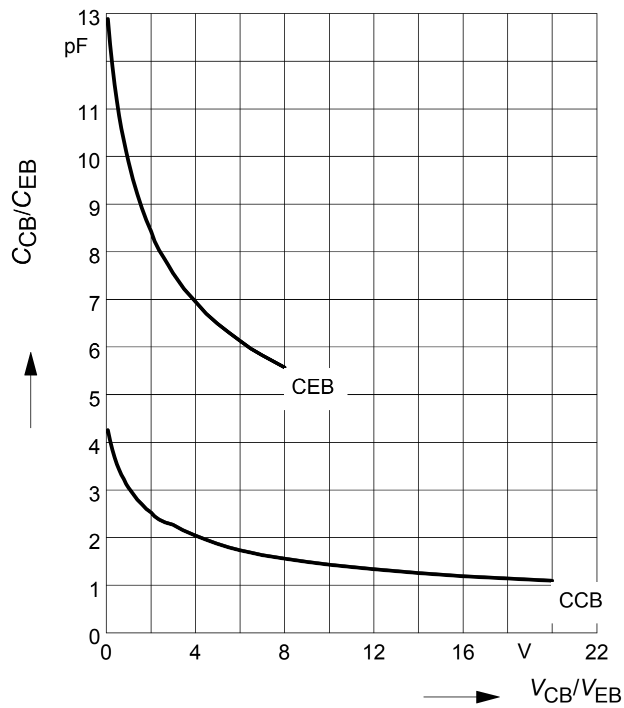
Transition frequency $f_T = f(I_C)$

V_{CE} = 5 V



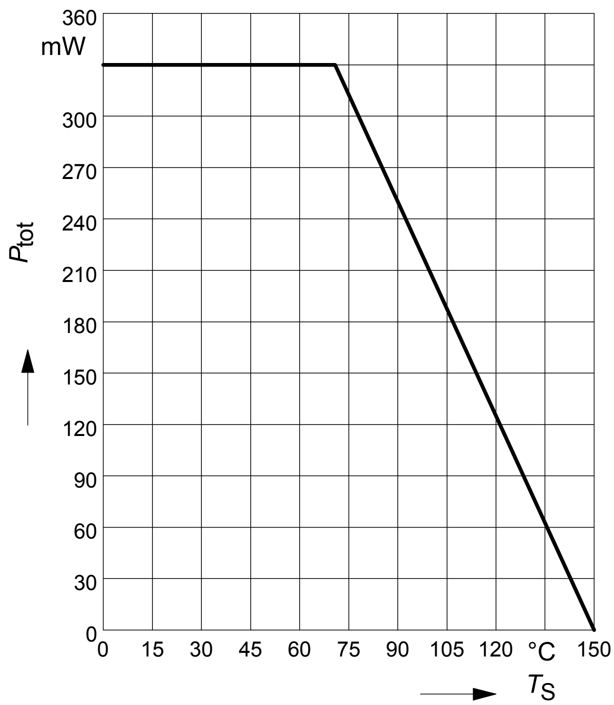
Collector-base capacitance $C_{cb} = f(V_{CB})$

Emitter-base capacitance $C_{eb} = f(V_{EB})$



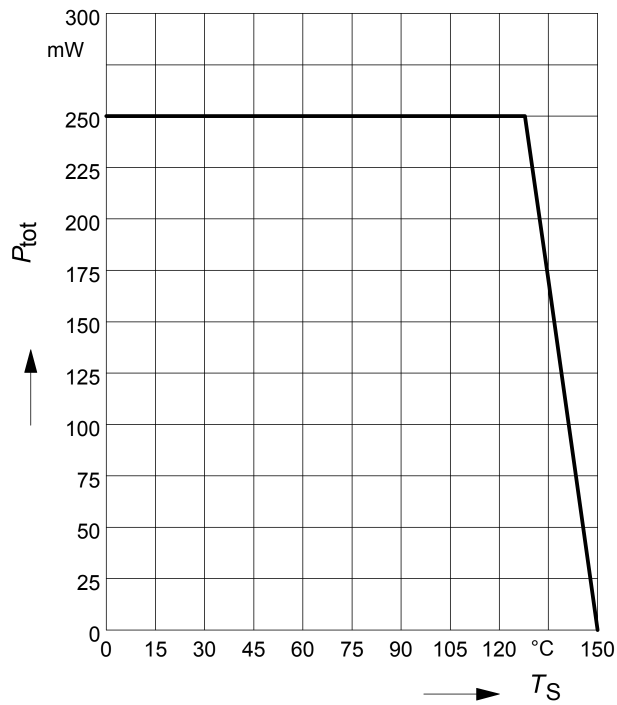
Total power dissipation $P_{tot} = f(T_S)$

BC846-BC850



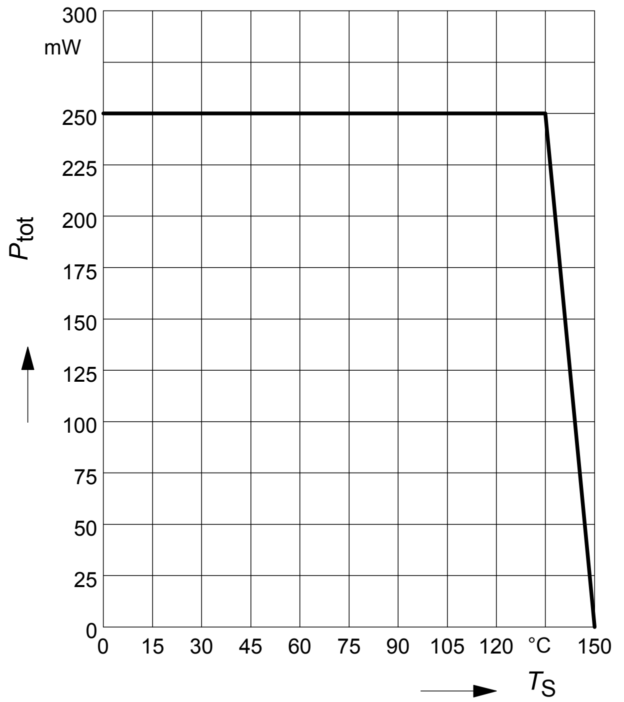
Total power dissipation $P_{tot} = f(T_S)$

BC847BF-BC850BF



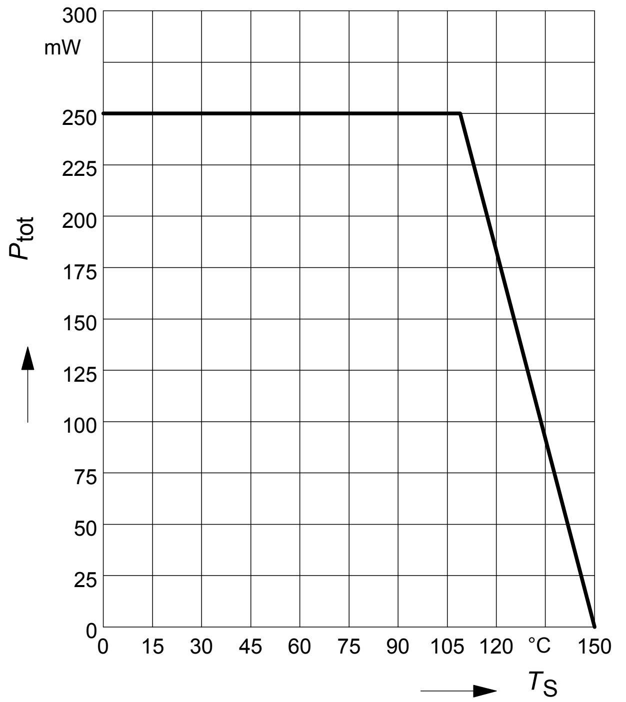
Total power dissipation $P_{tot} = f(T_S)$

BC847BL3 / BC848BL3



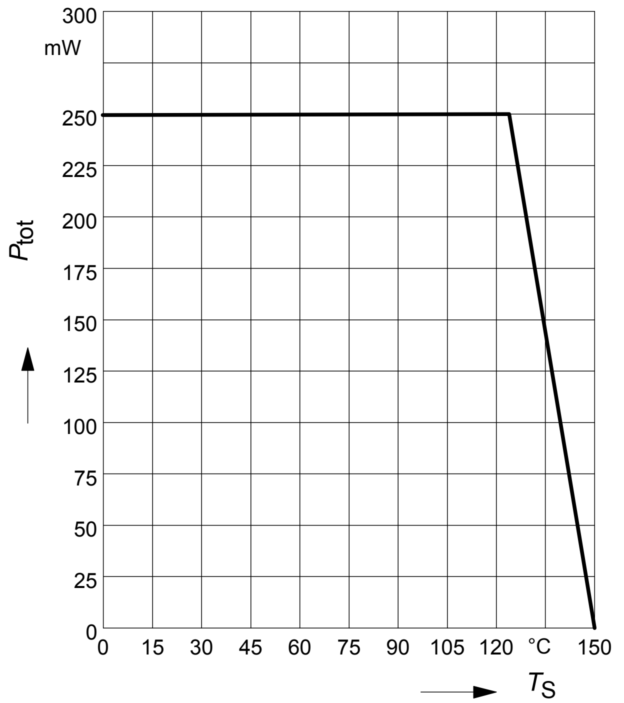
Total power dissipation $P_{tot} = f(T_S)$

BC847BT



Total power dissipation $P_{tot} = f(T_S)$

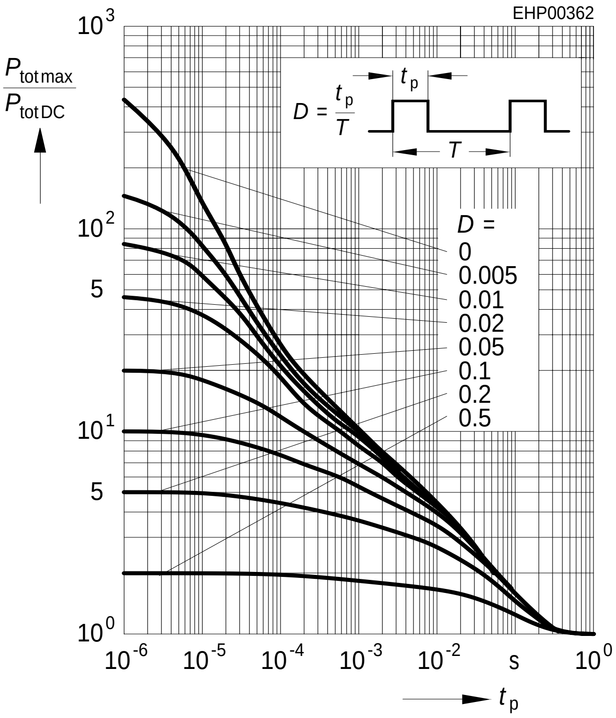
BC846W-BC850W



Permissible Pulse Load

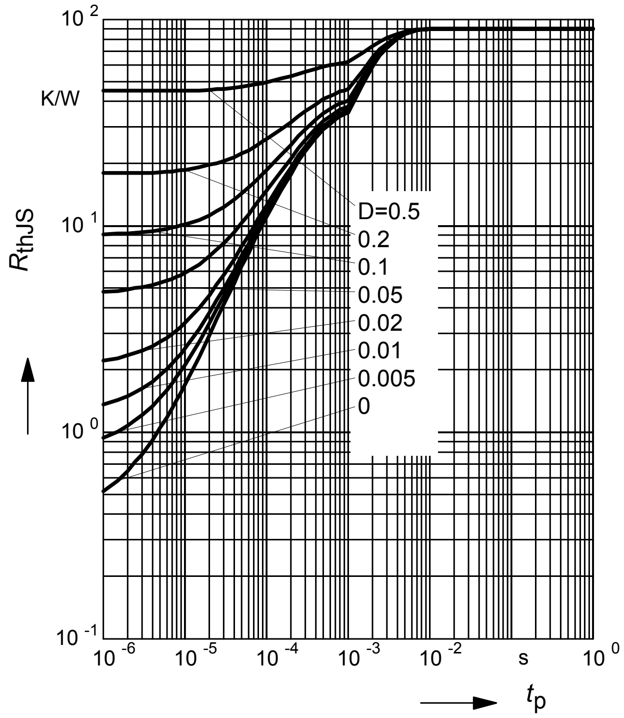
$P_{totmax}/P_{totDC} = f(t_p)$

BC846/W-BC850/W



Permissible Puls Load $R_{thJS} = f\ (t_p)$

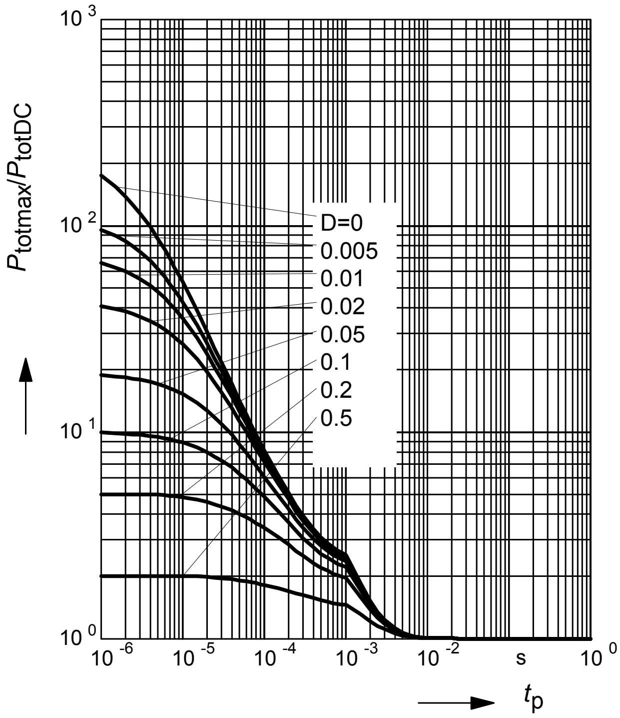
BC847BF-BC850BF



Permissible Pulse Load

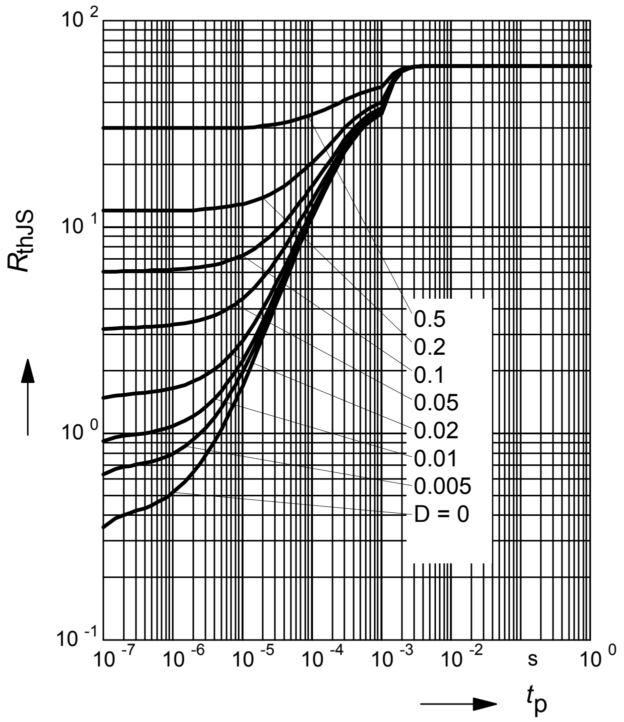
$P_{totmax}/P_{totDC} = f(t_p)$

BC847BF-BC850BF



Permissible Puls Load $R_{thJS} = f\ (t_p)$

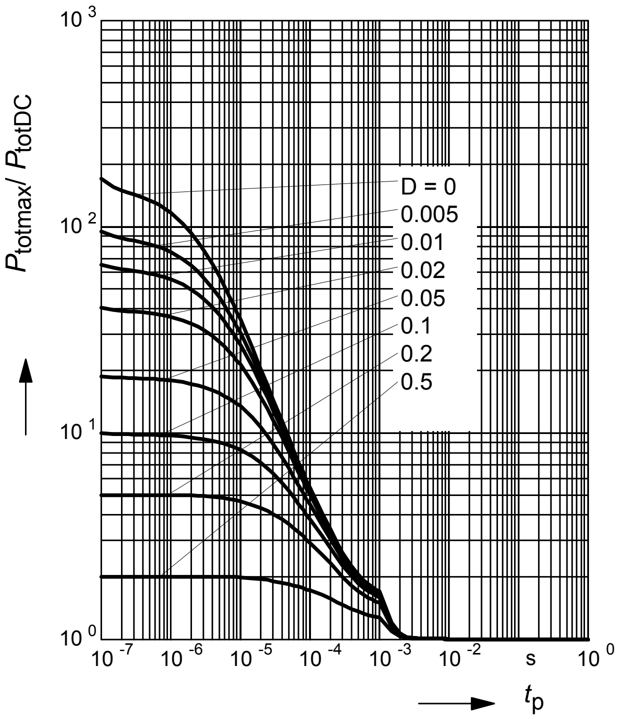
BC847BL3, BC848BL3



Permissible Pulse Load

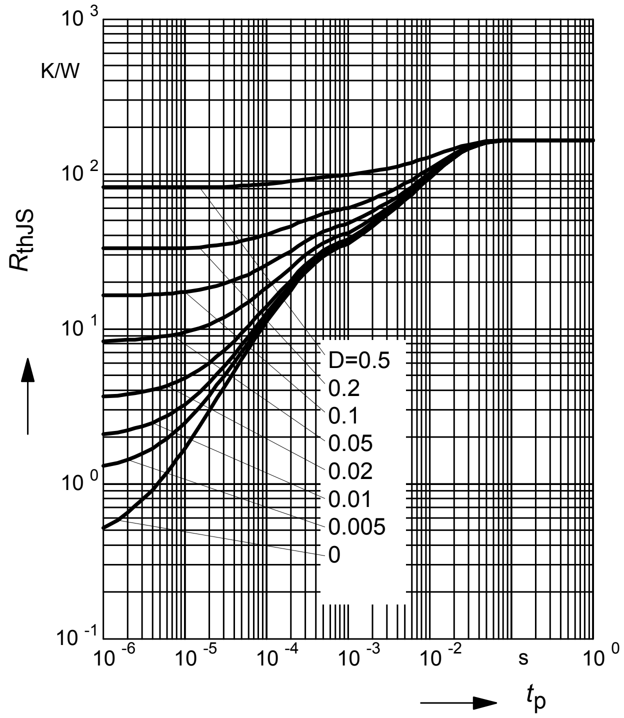
$P_{totmax}/P_{totDC} = f(t_p)$

BC847BL3, BC848BL3



Permissible Puls Load $R_{thJS} = f(t_p)$

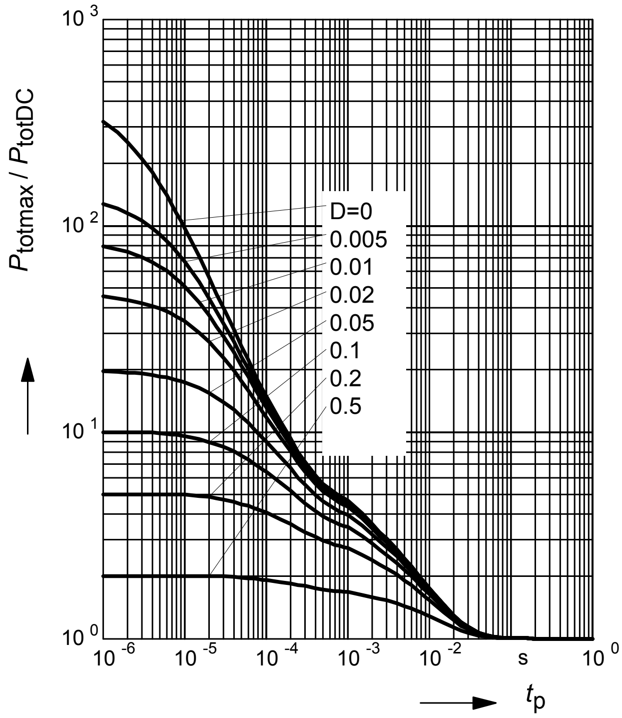
BC847BT



Permissible Pulse Load

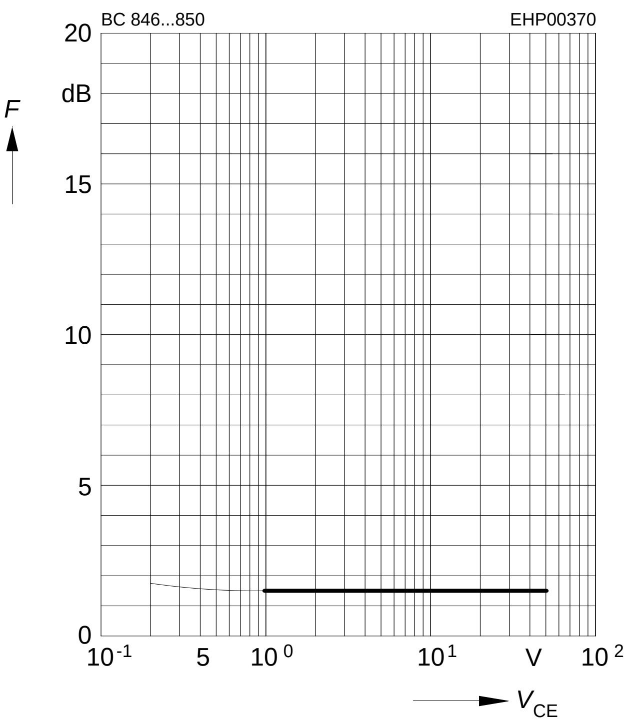
$P_{totmax}/P_{totDC} = f(t_p)$

BC847BT



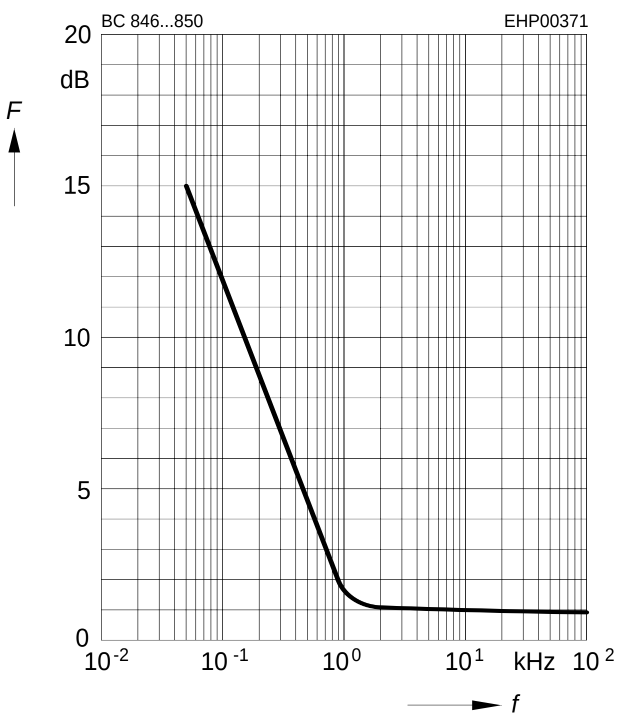
Noise figure $F = f(V_{CE})$

I_C = 0.2mA, R_S = 2kΩ , f = 1kHz

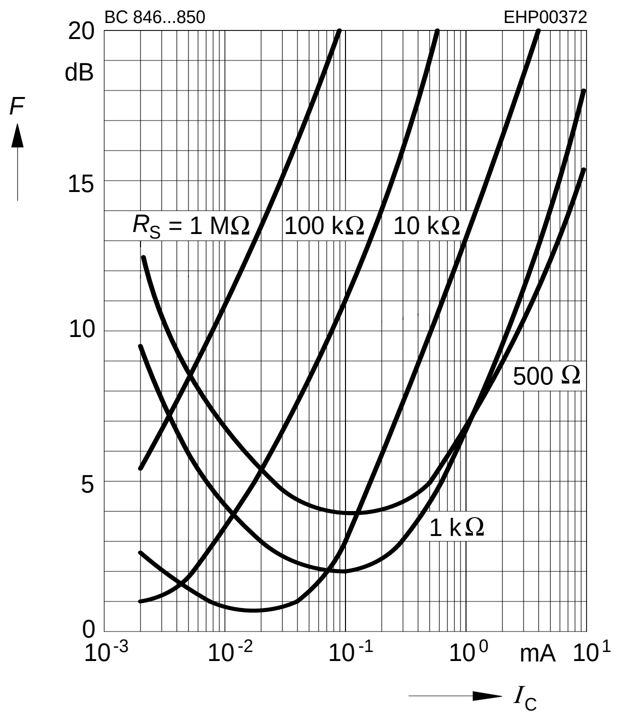


Noise figure $F = f(f)$

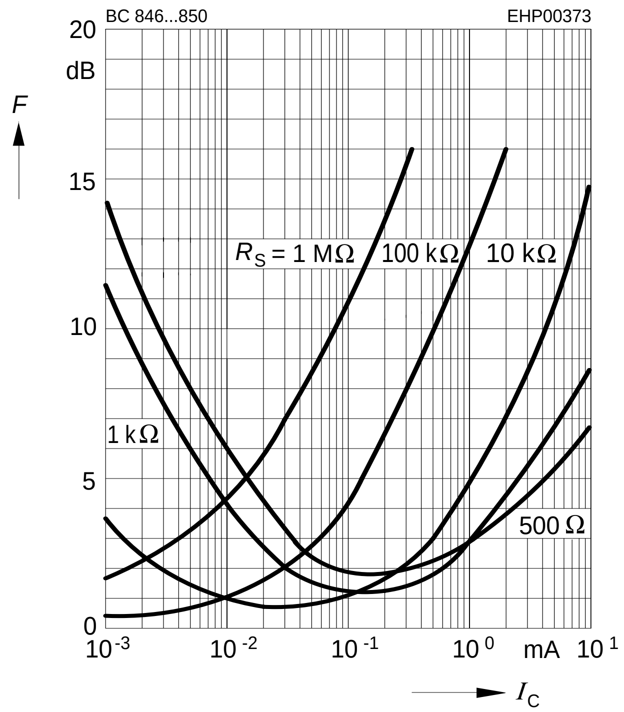
I_C = 0.2 mA, V_{CE} = 5V, R_S = 2 kΩ



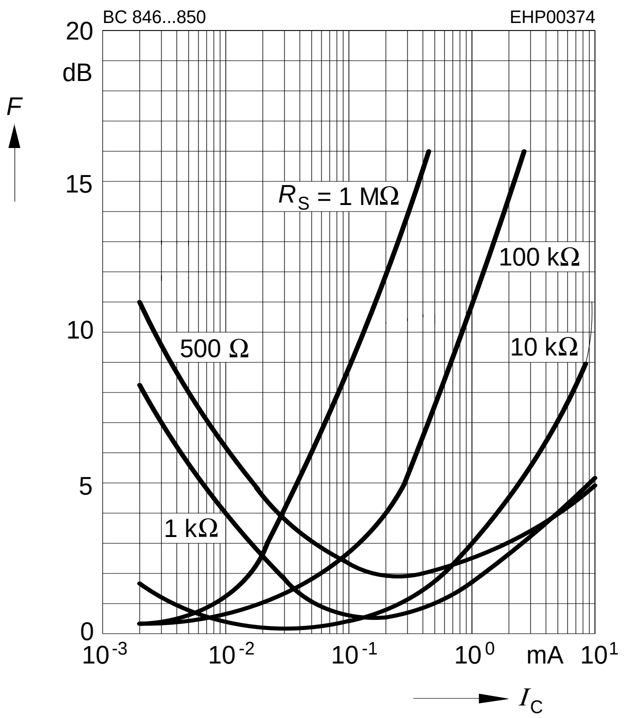
Noise figure $F = f(I_C)$
V_{CE} = 5V, f = 120Hz



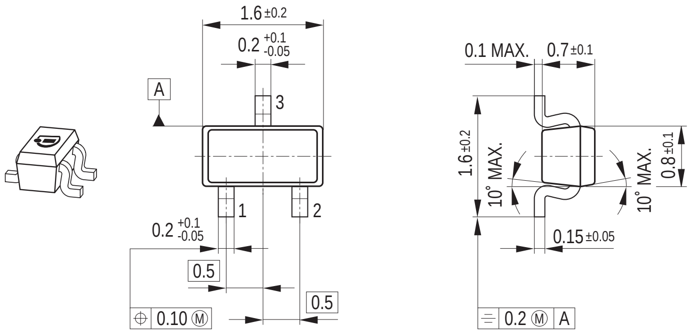
Noise figure $F = f(I_C)$
V_{CE} = 5V, f = 1kHz



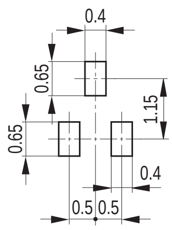
Noise figure $F = f(I_C)$
V_{CE} = 5V, f = 10kHz



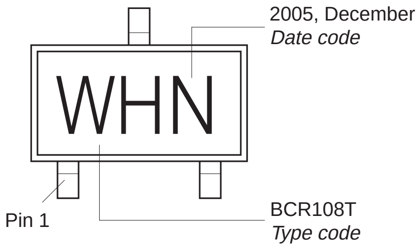
Package Outline



Foot Print

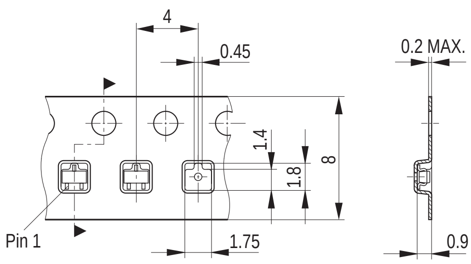


Marking Layout (Example)



Standard Packing

Reel ø180 mm = 3.000 Pieces/Reel
Reel ø330 mm = 10.000 Pieces/Reel



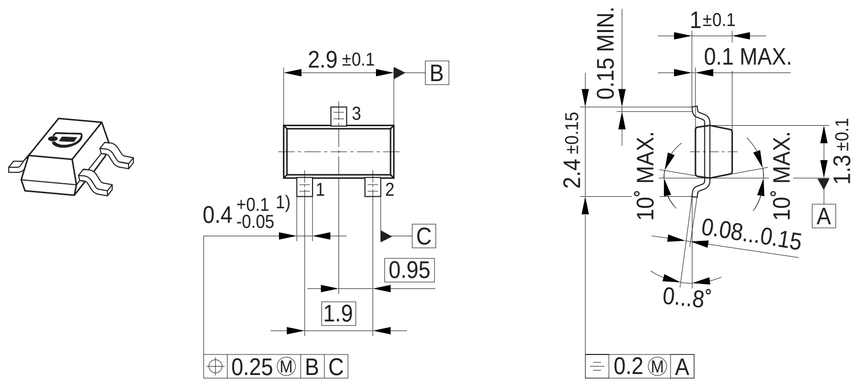
Date Code marking for discrete packages with one digit (SCD80, SC79, SC75[1)]) CES-Code

Month	2003	2004	2005	2006	2007	2008	2009	2010	2011	2012	2013	2014
01	a	p	A	P	a	p	A	P	a	p	A	P
02	b	q	B	Q	b	q	B	Q	b	q	B	Q
03	c	r	C	R	c	r	C	R	c	r	C	R
04	d	s	D	S	d	s	D	S	d	s	D	S
05	e	t	E	T	e	t	E	T	e	t	E	T
06	f	u	F	U	f	u	F	U	f	u	F	U
07	g	v	G	V	g	v	G	V	g	v	G	V
08	h	x	H	X	h	x	H	X	h	x	H	X
09	j	y	J	Y	j	y	J	Y	j	y	J	Y
10	k	z	K	Z	k	z	K	Z	k	z	K	Z
11	l	2	L	4	l	2	L	4	l	2	L	4
12	n	3	N	5	n	3	N	5	n	3	N	5

1) New Marking Layout for SC75, implemented at October 2005.

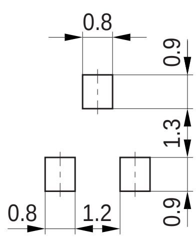
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Package Outline

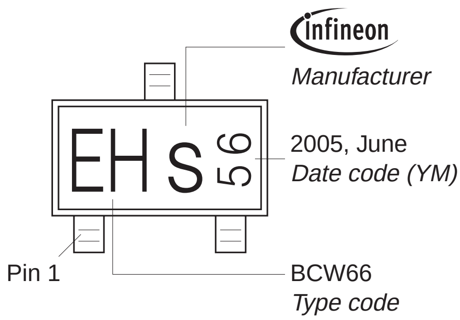


1) Lead width can be 0.6 max. in dambar area

Foot Print

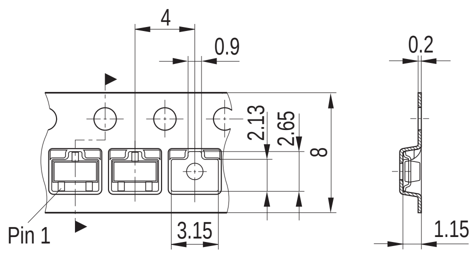


Marking Layout (Example)

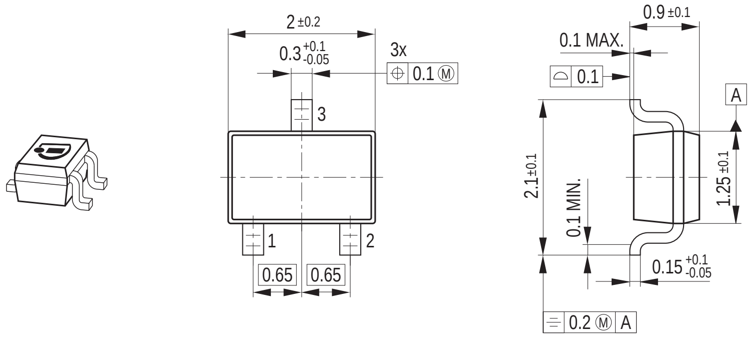


Standard Packing

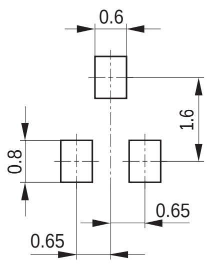
Reel ø180 mm = 3.000 Pieces/Reel
Reel ø330 mm = 10.000 Pieces/Reel



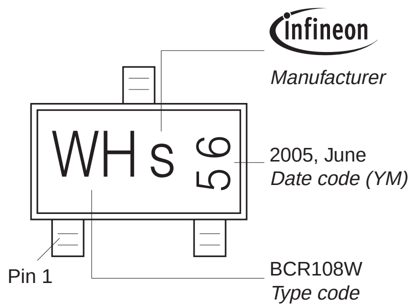
Package Outline



Foot Print

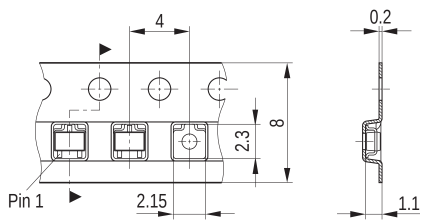


Marking Layout (Example)

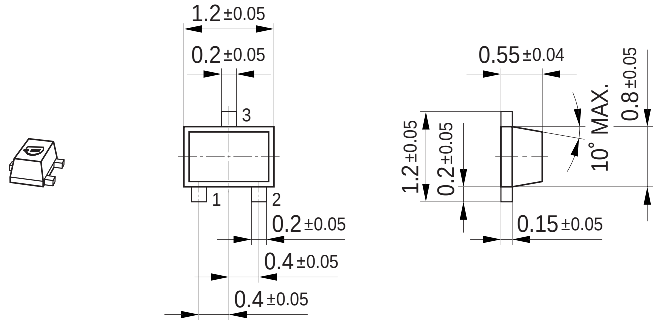


Standard Packing

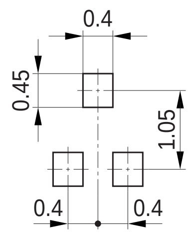
Reel ø180 mm = 3.000 Pieces/Reel
Reel ø330 mm = 10.000 Pieces/Reel



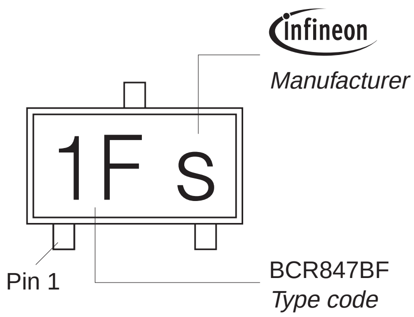
Package Outline



Foot Print

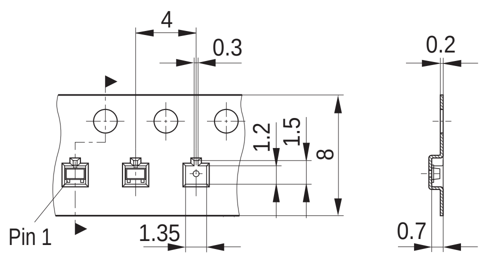


Marking Layout (Example)

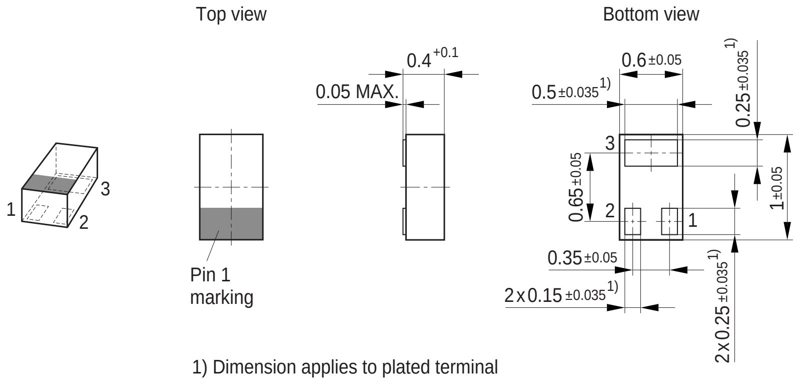


Standard Packing

Reel ø180 mm = 3.000 Pieces/Reel
Reel ø330 mm = 10.000 Pieces/Reel



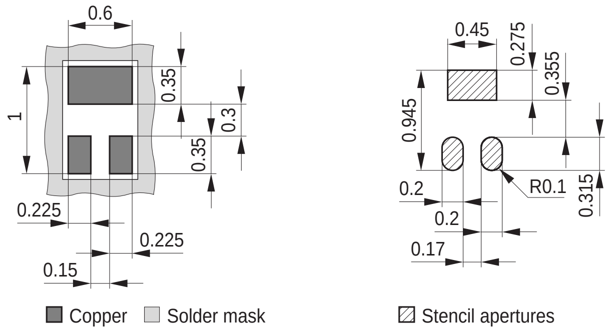
Package Outline



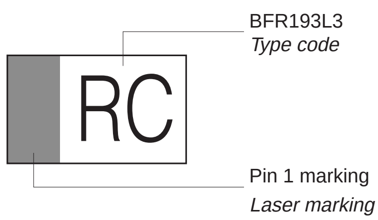
1) Dimension applies to plated terminal

Foot Print

For board assembly information please refer to Infineon website "Packages"

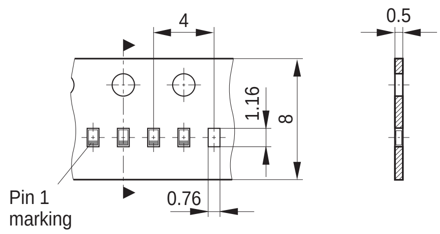


Marking Layout (Example)



Standard Packing

Reel ø180 mm = 15.000 Pieces/Reel



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